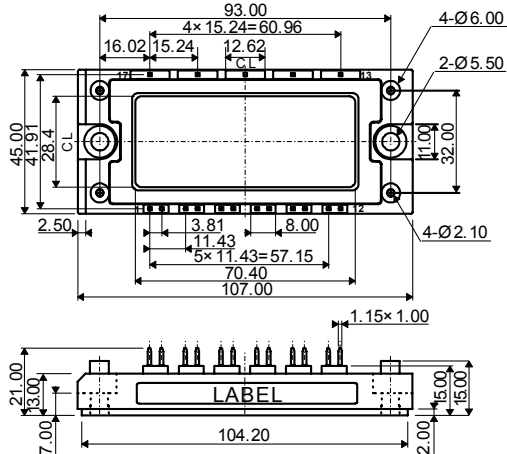
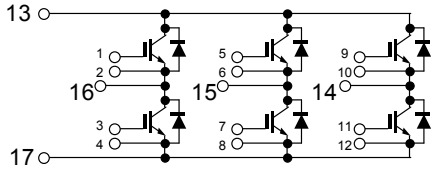


□ 回路図 : CIRCUIT

□ 外形寸法図 : OUTLINE DRAWING



Dimension: [mm]

□ 最大定格 : MAXIMUM RATINGS (T_c=25°C)

Item	Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CEs}	1, 200	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GES}	720	V
コレクタ電流 Collector Current	DC	I _C	50
	1ms	I _{CP}	100
コレクタ損失 Collector Power Dissipation	P _C	250	W
接合温度 Junction Temperature Range	T _J	-40~+150	°C
保存温度 Storage Temperature Range	T _{stg}	-40~+125	°C
絶縁耐圧(Terminal to Base AC, 1 minute) Isolation Voltage	V _{ISO}	2,500	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	F _{tor}	2 (20.4)
	Busbar to Main Terminal		-

□ 電気的特性 : ELECTRICAL CHARACTERISTICS (T_c=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I _{CEs}	V _{CE} = 1200V, V _{GE} = 0V	-	-	1.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current	I _{GES}	V _{GE} = 720V, V _{CE} = 0V	-	-	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 50A, V _{GE} = 15V	-	1.9	2.4	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 50mA	4.0	-	8.0	V
入力容量 Input Capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	4,200	-	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	t _r	-	0.25	0.45	μs
	ターンオン時間 Turn-on Time	t _{on}	-	0.40	0.70	
	下降時間 Fall Time	t _f	-	0.25	0.35	
	ターンオフ時間 Turn-off Time	t _{off}	-	0.80	1.10	

□ フリーホイールダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS (T_c=25°C)

Item	Symbol	Rated Value	Unit
順電流 Forward Current	DC	I _F	50
	1ms	I _{FM}	100

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V _F	I _F = 50A, V _{GE} = 0V	-	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t _{rr}	I _F = 50A, V _{GE} = -10V di/dt= 100A/μs	-	0.2	0.3	μs

□ 熱的特性 : THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	R _{th(j-c)}	Junction to Case	-	-	0.5
	Diode			-	-	1.0

Fig.1- Output Characteristics (Typical)

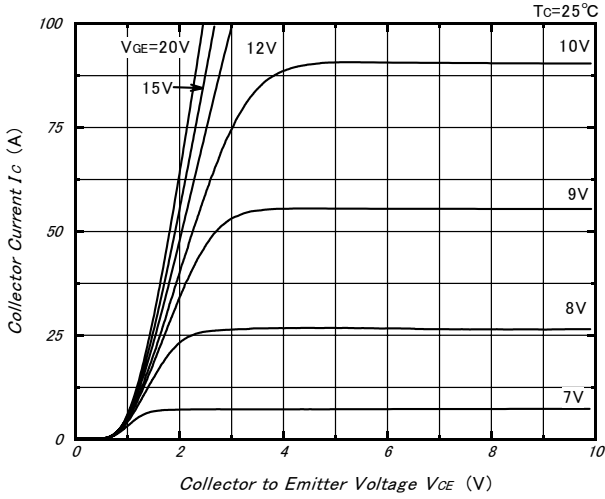


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

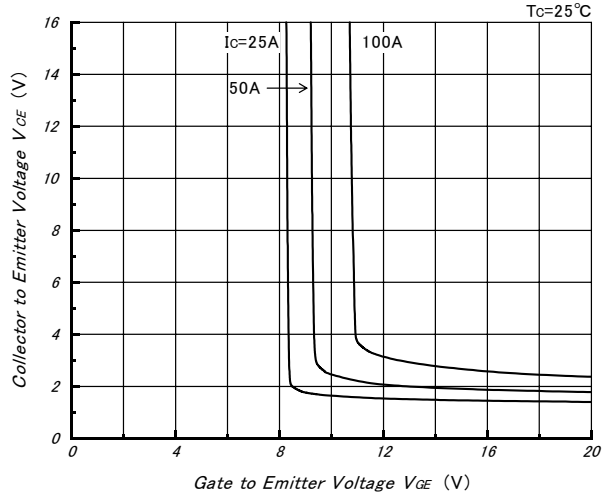


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

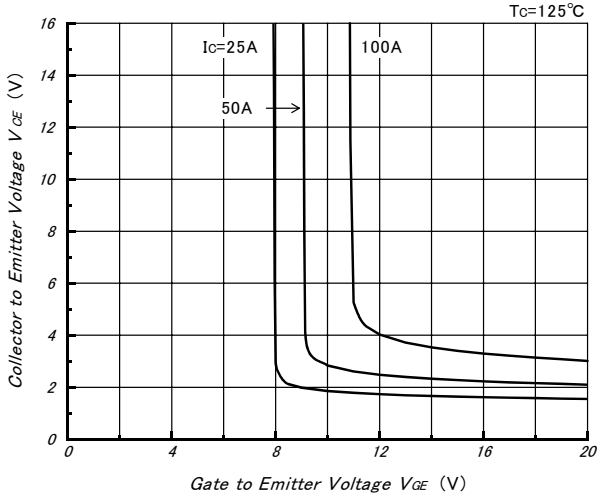


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

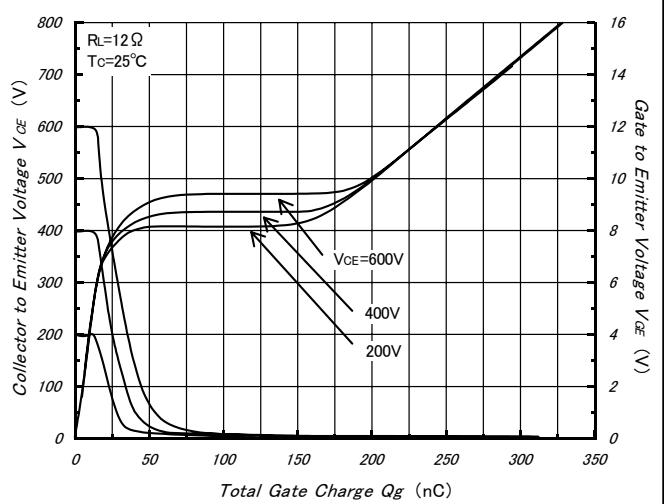


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

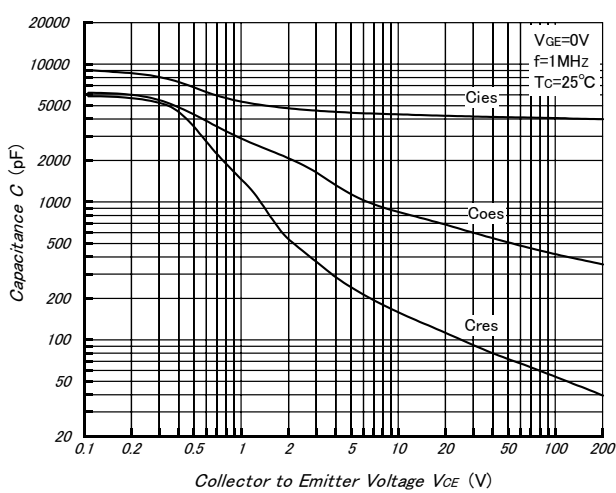


Fig.6- Collector Current vs. Switching Time (Typical)

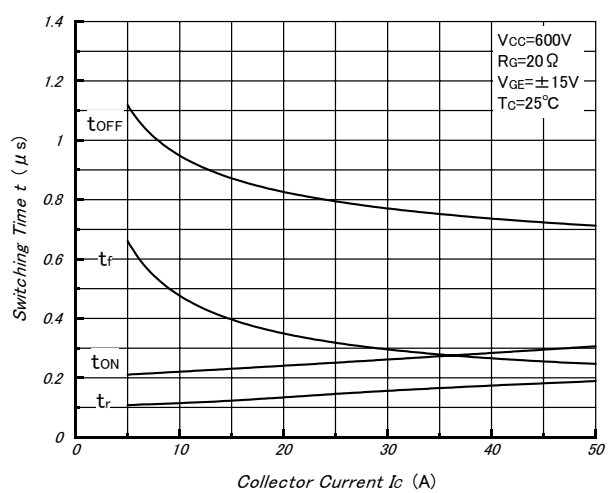


Fig.7- Series Gate Impedance vs. Switching Time (Typical)

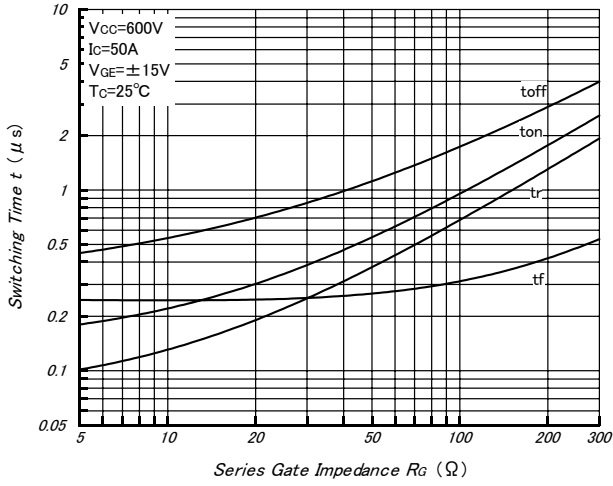


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

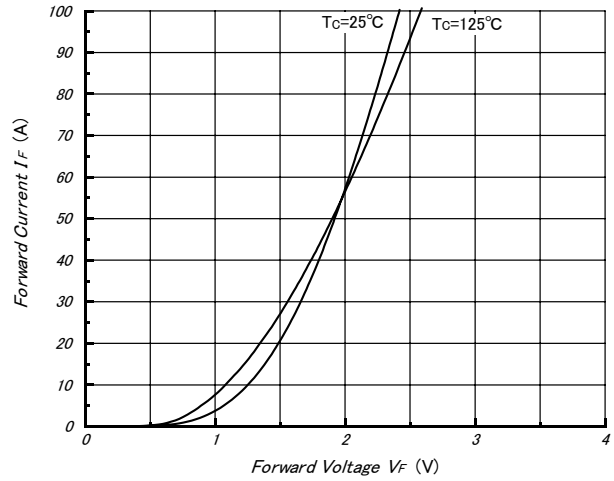


Fig.9- Reverse Recovery Characteristics (Typical)

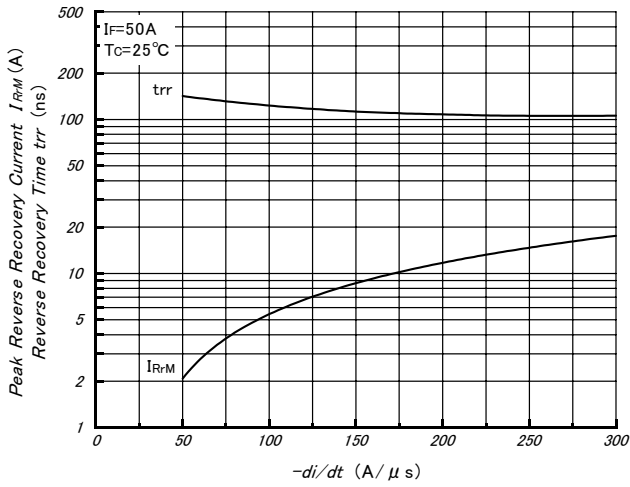


Fig.10- Reverse Bias Safe Operating Area

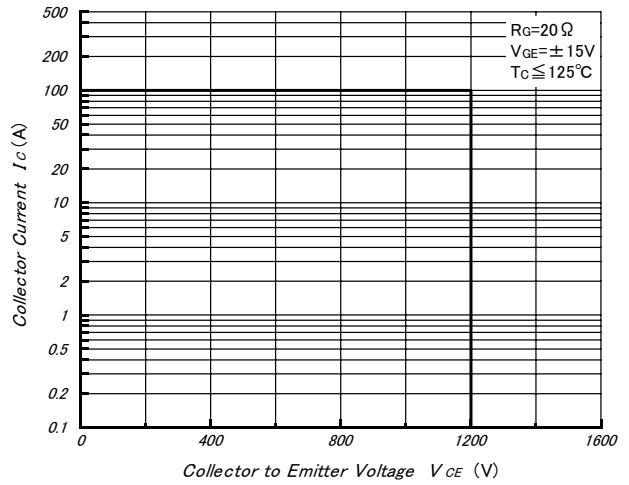


fig11-Transient Thermal Impedance

